



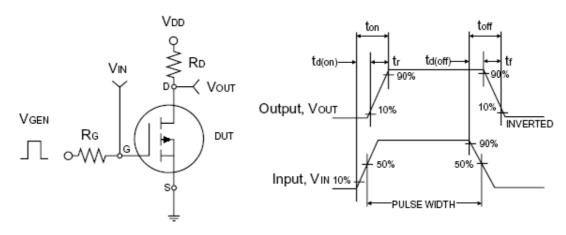
20V N-Channel MOSFET

Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static ^(Note 2)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	V _{GS(TH)}	-	0.65	1	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}	1		±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I _{DSS}	-		1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	30			Α
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 4.5A$	R _{DS(ON)}	1	23	30	mΩ
	$V_{GS} = 2.5V, I_D = 3.5A$		1	25	35	
	$V_{GS} = 1.8V, I_D = 2.0A$		1	35	45	
Forward Transconductance	$V_{DS} = 10V, I_{D} = 6A$	g _{fs}	1	40		S
Diode Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	V_{SD}		0.8	1.2	V
Dynamic ^(Note 3)						
Total Gate Charge	$V_{DS} = 10V, I_D = 4.5A,$ $V_{GS} = 4.5V$	Q_g		11.2	14	nC
Gate-Source Charge		Q_gs		1.4		
Gate-Drain Charge		Q_{gd}		2.2		
Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ $f = 1.0MHz$	C_{iss}		500		pF
Output Capacitance		C_{oss}	1	300		
Reverse Transfer Capacitance		C_{rss}	1	140		
Switching ^(Note 4)						
Turn-On Delay Time	$V_{DD} = 10V, R_L = 10\Omega,$ $I_D = 1A, V_{GEN} = 4.5V,$ $R_G = 6\Omega$	t _{d(on)}	1	15	25	ns
Turn-On Rise Time		t _r	-	30	60	
Turn-Off Delay Time		t _{d(off)}		35	70	
Turn-Off Fall Time		t _f		15	45	

Notes:

- 1. Pulse width limited by the maximum junction temperature
- 2. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%
- 3. For DESIGN AID ONLY, not subject to production testing.
- 4. Switching time is essentially independent of operating temperature.



2

Switching Test Circuit

Switchin Waveforms



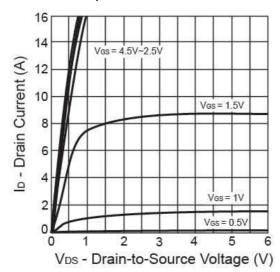
TSM4424

20V N-Channel MOSFET

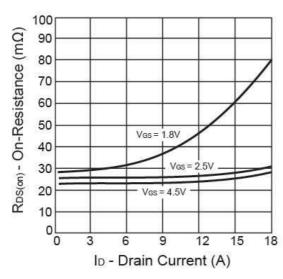


Electrical Characteristics Curve

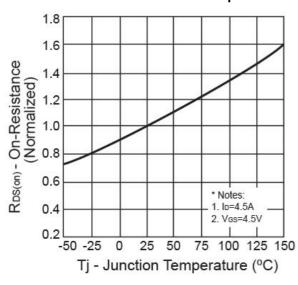
Output Characteristics



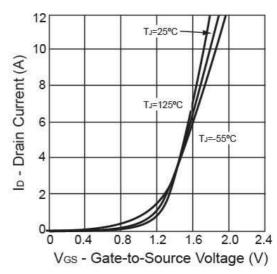
On-Resistance vs. Drain Current



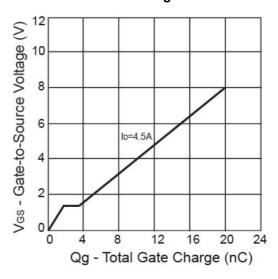
On-Resistance vs. Junction Temperature



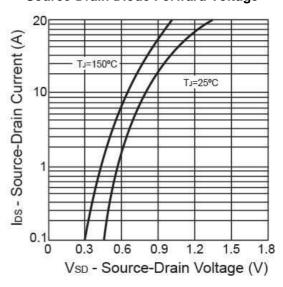
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



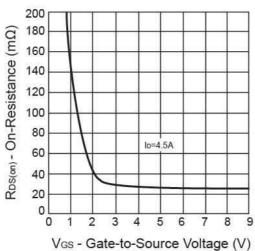
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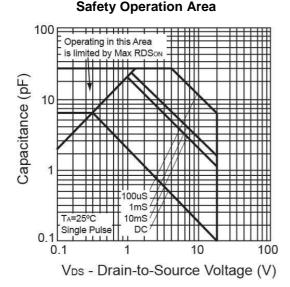


Electrical Characteristics Curve

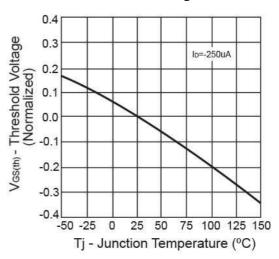
On-Resistance vs. Gate-Source Voltage



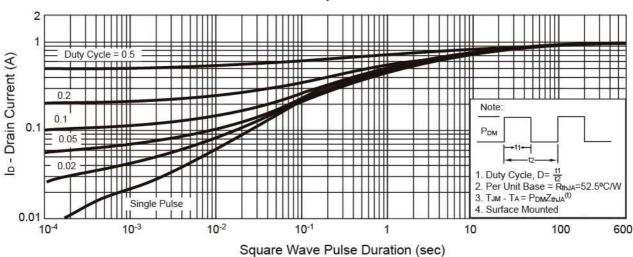
vos cute to course voltage



Threshold Voltage



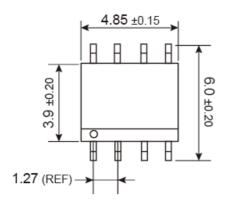
Normalized Thermal Transient Impedance, Junction-to-Ambient

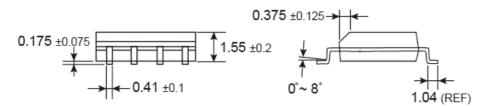






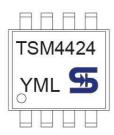
SOP-8 Mechanical Drawing





Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



TSM4424 20V N-Channel MOSFET

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